Abstracts

X-Band Silicon Power Transistor

H.-T. Yuan, J.B. Kruger and Y.-S. Wu. "X-Band Silicon Power Transistor." 1975 MTT-S International Microwave Symposium Digest of Technical Papers 75.1 (1975 [MWSYM]): 73-75.

A four cell silicon bipolar power transistor exhibiting 1.0 watts cw output power with 6 dB power gain and 30% collector efficiency at 8 GHz has been developed. The transistor has 1µm metal contacts and 0.5 µm emitter width. Direct electron-beam slice writing was applied to define the fine geometries.

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